

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-21 (Cancelled)

22. (Currently Amended) A polycide gate structure, comprising:
- (1) a polysilicon structure formed upon said a substrate and having laterals;
 - (2) an insulating structure disposed on said laterals of said polysilicon structure for insulating said polysilicon structure;
 - (3) a silicide structure formed upon said polysilicon structure and having laterals; and
 - (4) a protecting structure ~~disposed~~ formed by means of chemical vapor deposition (CVD) on said laterals of said silicide structure ~~of~~ for protecting said silicide structure.
23. (Currently Amended) The structure as claimed in claim 22, wherein said insulating layer structure is silicon dioxide (SiO₂).
24. (Currently Amended) The structure as claimed in claim 22, wherein said silicide ~~layer~~ structure upon said polysilicon ~~layer~~ structure comprises a barrier, a tungsten layer and a silicon nitride (SiNX) layer in sequence.
25. (Original) The structure as claimed in claim 24, wherein said barrier is titanium nitride (TiN).
26. (Cancelled)
27. (Currently Amended) The structure as claimed in claim 22, wherein said protecting ~~layer~~ structure has a thickness ranged from 50 to 500 Å.
28. (Currently Amended) The structure as claimed in claim 22, wherein said protecting ~~layer~~ structure is silicon nitride (SiNX).

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29. (Currently Amended) The structure method as claimed in claim 22, wherein said ~~polysilicide~~ polysilicon structure is defined via an anisotropic dry etcher.
30. (Original) The structure as claimed in claim 22, wherein said insulating structure is formed by means of a dry oxidation method.
31. (Currently Amended) The structure as claimed in claim 22, wherein said ~~polysilicide~~ silicide structure is defined via anisotropic dry etcher.
32. (Original) The structure as claimed in claim 22, wherein said protecting structure is defined via an anisotropic dry etcher.

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